

1 1. A method comprising:  
2 forming an integrated inductor over a substrate;  
3 forming an aperture underneath said inductor  
4 through said substrate from the back side of said  
5 substrate; and  
6 filling said aperture with a dielectric material.

1 2. The method of claim 1 including covering the  
2 backside of said substrate with a dielectric material.

1 3. The method of claim 2 including filling said  
2 aperture and covering said substrate back side with the  
3 same dielectric material.

1 4. The method of claim 1 including forming a field  
2 oxide formed over said substrate and forming said inductor  
3 over said field oxide region.

1 5. The method of claim 1 including forming said  
2 aperture completely through said substrate.

1 6. The method of claim 5 including supporting said  
2 inductor over said aperture in said substrate on an  
3 intervening layer between said substrate and said inductor.

1           7.    A method comprising:  
2                forming a layer over a substrate;  
3                forming an integrated inductor over said layer  
4   and said substrate;  
5                forming an aperture underneath said inductor  
6   completely through said substrate from the back side of  
7   said substrate; and  
8                filling said aperture with a dielectric material.

1           8.    The method of claim 7 including covering the back  
2   side of said substrate with a dielectric material.

1           9.    The method of claim 8 including filling said  
2   aperture and covering said substrate back side with the  
3   same dielectric material.

1           10.   The method of claim 7 wherein forming said layer  
2   over said substrate includes forming a field oxide over  
3   said substrate and forming said inductor over said field  
4   oxide.

1           11.   The method of claim 7 including forming said  
2   aperture completely through said substrate to said layer.

1           12. The method of claim 11 including supporting said  
2 inductor over said aperture and said substrate on said  
3 layer.

1           13. An integrated circuit comprising:  
2           a substrate;  
3           an integrated inductor formed over a first side  
4 of said substrate;  
5           an aperture formed in said substrate from a  
6 second side of said substrate underneath said inductor; and  
7           a dielectric material formed in said aperture.

1           14. The circuit of claim 13 including an intervening  
2 layer between said inductor and said substrate.

1           15. The circuit of claim 14 wherein said intervening  
2 layer is a field oxide region.

1           16. The circuit of claim 14 wherein said aperture is  
2 formed completely through said substrate to said  
intervening layer.

1           17. The circuit of claim 16 wherein said aperture  
2 encompasses the entire region beneath said integrated  
3 inductor.

1           18. An integrated circuit comprising:  
2           a substrate;  
3           an inductor formed over a first side of said  
4 substrate;  
5           an aperture formed in said substrate from a  
6 second side of said substrate underneath said inductor and  
7 extending completely through said substrate from said  
8 second side of said substrate to said first side of said  
9 substrate;  
10           a dielectric material filling said aperture;  
11           a dielectric material also coating the back side  
12 of said substrate; and  
13           an intervening layer between said inductor and  
14 said substrate.

1           19. The circuit of claim 18 wherein said intervening  
2 layer is a field oxide region.

1           20. The circuit of claim 19 wherein said aperture  
2 encompasses the entire region beneath said integrated  
3 inductor.

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